2SK1340

Silicon N-Channel MOS FET

HITACHI

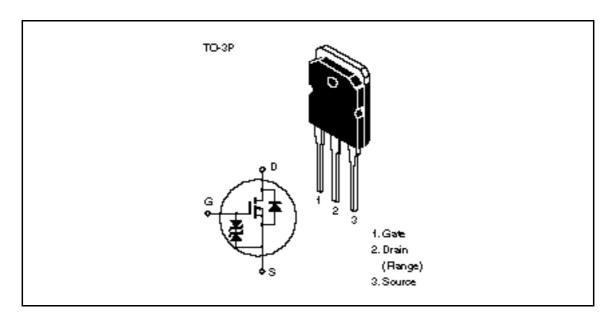
Application

High speed power switching

Features

- · Low on-resistance
- High speed switching
- · Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline





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Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{\scriptscriptstyle DSS}$	900	V
Gate to source voltage	$V_{\sf GSS}$	±30	V
Drain current	I _D	5	A
Drain peak current	l _{D(pulse)} *1	12	А
Body to drain diode reverse drain current	I _{DR}	5	А
Channel dissipation	Pch*2	100	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW 10 µs, duty cycle 1%

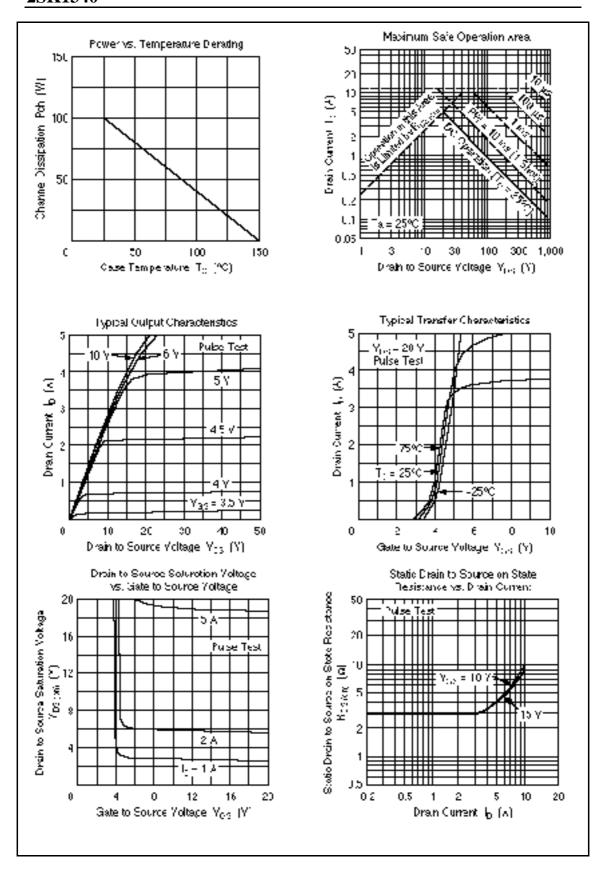
2. Value at T_c = 25°C

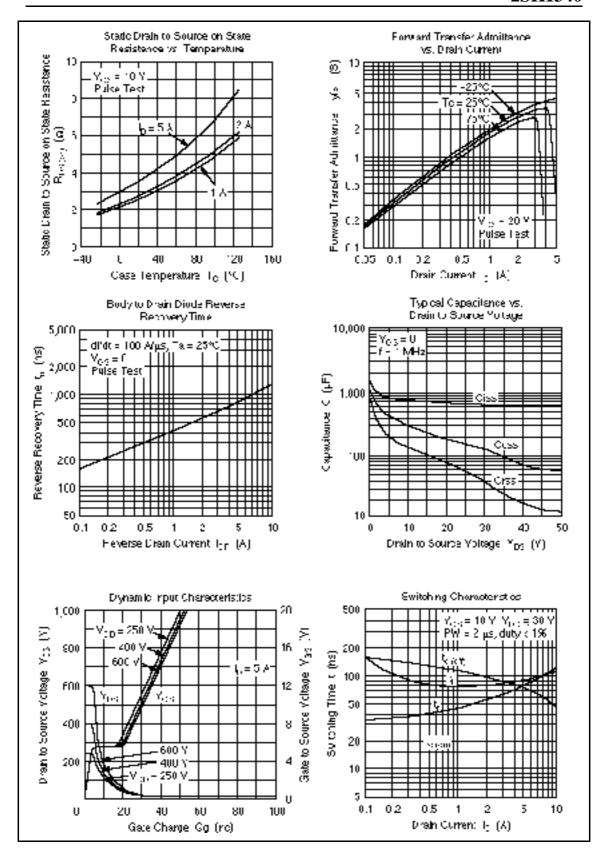
Electrical Characteristics ($Ta = 25^{\circ}C$)

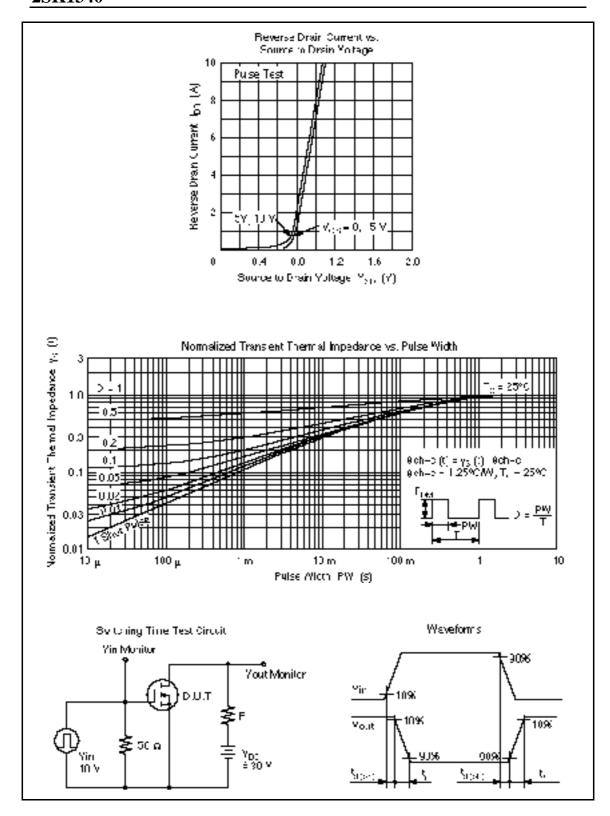
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	900	_	_	V	$I_{D} = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	250	μΑ	$V_{DS} = 720 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	2.0	_	3.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{\mathrm{DS(on)}}$	_	3.0	4.0		$I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	yfs	2.0	3.2	_	S	$I_D = 3 \text{ A}, V_{DS} = 20 \text{ V}^{*1}$
Input capacitance	Ciss	_	740	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	305	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	150	_	pF	
Turn-on delay time	t _{d(on)}	_	15	_	ns	$I_D = 3 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t _r	_	70	_	ns	$R_L = 10$
Turn-off delay time	t _{d(off)}	_	90	_	ns	
Fall time	t _f	_	90	_	ns	
Body to drain diode forward voltage	V_{DF}		0.9	_	V	$I_{F} = 5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}	_	900	_	ns	$I_F = 5 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A/}\mu\text{s}$

Note: 1. Pulse test

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